

# 30V Dual N-Channel MOSFET



SOP-8

#### Pin Definition:



1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2

. Gate 2 5. Drain 2

#### PRODUCT SUMMARY

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)	I <sub>D</sub> (A)
30	15 @ V <sub>GS</sub> = 10V	11
	24 @ V <sub>GS</sub> = 4.5V	10

### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

### **Application**

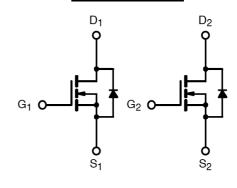
- Load Switch
- PWM Application

## **Ordering Information**

Part No.	Package	Packing
TSM4416DCS RL	SOP-8	2.5Kpcs / 13" Reel
TSM4416DCS RLG	SOP-8	2.5Kpcs / 13" Reel

Note: "G" denotes Halogen Free Product.

## **Block Diagram**



**Dual N-Channel MOSFET** 

## **Absolute Maximum Rating** (T<sub>A</sub>=25°C, unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current		I <sub>D</sub>	11	А	
Pulsed Drain Current		I <sub>DM</sub>	40	А	
Continuous Source Current (Diode Cond	uction) <sup>a,b</sup>	I <sub>S</sub>	2.6	А	
Mayira ya Dayya Dissination	Ta = 25°C	Б	2.5	10/	
Maximum Power Dissipation	1.6	W			
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance Junction to Foot	R⊖ <sub>JF</sub>	25	°C/W
Thermal Resistance Junction to Ambient	RO <sub>JA</sub>	50	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 5$  sec.



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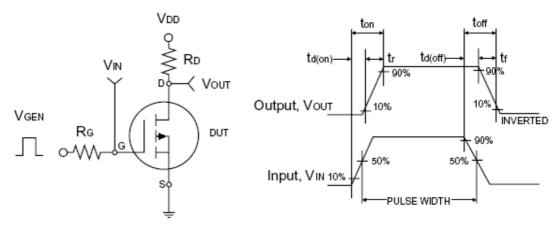


**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.8	3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I <sub>DSS</sub>			-1.0	uA
Drain Course On State Besistance	$V_{GS} = 10V, I_D = 10A$			12	15	m O
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 10A$	R <sub>DS(ON)</sub>		16	24	mΩ
Forward Transconductance	$I_{S} = 1A, V_{GS} = 0V$	g <sub>fs</sub>		17		S
Diode Forward Voltage	$V_{GS} = 0V, I_D = 250uA$	$V_{SD}$	1	0.71	1.0	V
Dynamic <sup>b</sup>						
Total Gate Charge	\/ 45\/   400	$Q_g$		7.7	10.01	
Gate-Source Charge	$V_{DS} = 15V, I_{D} = 10A,$ $V_{GS} = 5V$	$Q_gs$		1.6	2.08	nC
Gate-Drain Charge	V <sub>GS</sub> = 5 V	$Q_{gd}$		3.1	4.03	
Input Capacitance	\	C <sub>iss</sub>	1	890	-	
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C <sub>oss</sub>	1	159.6	1	pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		83.2		
Switching <sup>b,c</sup>						
Turn-On Delay Time		t <sub>d(on)</sub>	1	11.1	22.2	
Turn-On Rise Time	$V_{DD} = 15V, I_D = 10A,$	t <sub>r</sub>	-	8.4	16.8	~ C
Turn-Off Delay Time	$V_{GEN} = 10V, R_G = 0.3\Omega$	t <sub>d(off)</sub>		25.3	50.6	nS
Turn-Off Fall Time		t <sub>f</sub>		2.8	5.6	

### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



Switching Test Circuit

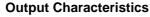
Switchin Waveforms

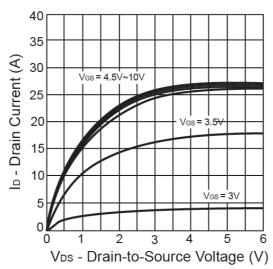


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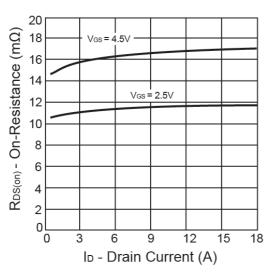


### **Electrical Characteristics Curve** (T<sub>A</sub>=25°C, unless otherwise noted)

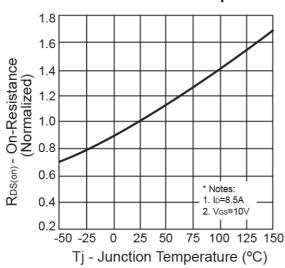




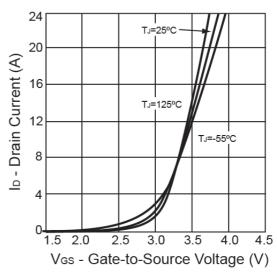
#### **On-Resistance vs. Drain Current**



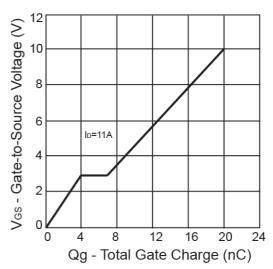
**On-Resistance vs. Junction Temperature** 



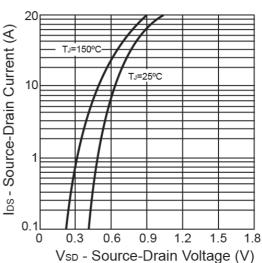
### **Transfer Characteristics**



**Gate Charge** 



**Source-Drain Diode Forward Voltage** 



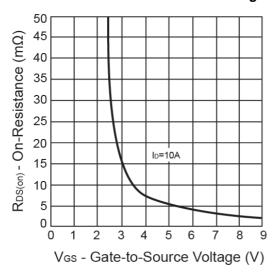


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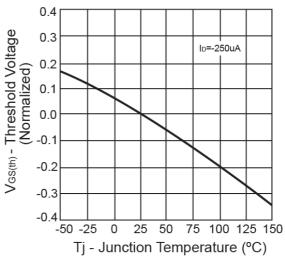


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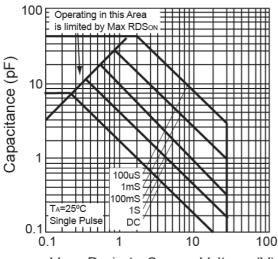
### On-Resistance vs. Gate-Source Voltage



# Threshold Voltage



#### **Safety Operation Area**



V<sub>DS</sub> - Drain-to-Source Voltage (V)

Version: B12

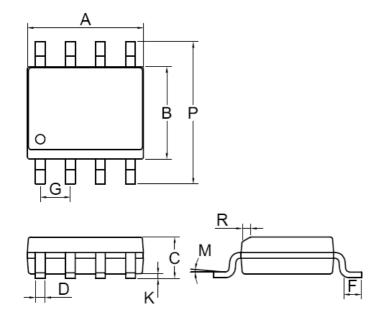
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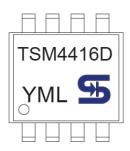


# **SOP-8 Mechanical Drawing**



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	00	7º	00	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

# **Marking Diagram**



Y = Year Code

M = Month Code

(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)

Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

Version: B12



# TSM4416D 30V Dual N-Channel MOSFET

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